

## **DESCRIPTION:**

This document describes Aplus 512M x 72-bit 4GB DDR2-533 CL4 SDRAM (Synchronous DRAM) Registered ECC memory module. The components on this module include thirty-six 256M x 4-bit (8Banks) DDR2-533 SDRAM in FBGA packages. This 240-pin DIMM uses gold contact fingers and requires +1.8V. The electrical and mechanical specifications are as follows:

## **FEATURES:**

- JEDEC standard 1.8V ± 0.1V Power supply
- All inputs and outputs SSTL\_1.8 compatible
- Max clock Freq: 267Mhz
- Double-data-rate architecture; two data transfers per clock cycle
- Bidirectional data strobe (DQS)
- Differential clock inputs (CK and CK)
- DLL aligns DQ and DQS transition with CK transition
- Programmable Read latency 4 (clock)
- Programmable Burst length (4,8)
- Programmable Burst type (sequential & interleave)
- Timing Reference: CL-tRCD-tRP (4-4-4)
- Edge aligned data output, center aligned data input
- Auto & Self refresh, 7.8us refresh interval (8K/64ms refresh)
- Error Check Correction ( ECC ) Capability
- High temperature self-refresh Entry enableble features
- PASR ( Partial array self refresh )
- OCD ( Off-chip driver impedance adjustment )
- ODT ( On-die termination )
- Serial presence detect with EEPROM

## **PERFORMANCE:**

|                                 |                              |
|---------------------------------|------------------------------|
| Clock Cycle Time ( tCK )        | 5ns (min.) /8ns (max.)       |
| Row Cycle Time ( tRC )          | 55ns (min.)                  |
| Refresh Row Cycle Time ( tRFC ) | 105ns (min.)                 |
| Row Active Time ( tRAS )        | 40ns (min.) /70,000ns (max.) |
| Operating Temperature           | 0 °C ~ 85 °C                 |
| Storage Temperature             | -55 °C ~ +100 °C             |

